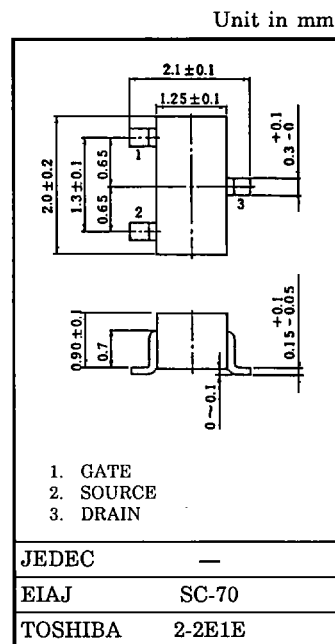


HIGH SPEED SWITCHING APPLICATIONS.
ANALOG SWITCH APPLICATIONS.

- High Input Impedance.
- Low Gate Threshold Voltage : $V_{th} = 0.5 \sim 1.5V$
- Excellent Switching Times : $t_{on} = 0.16\mu s$ (typ.)
 $t_{off} = 0.15\mu s$ (typ.)
- Small Package.
- Enhancement-Mode

MAXIMUM RATINGS ($T_a = 25^\circ C$)

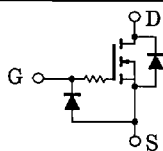
CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GSS}	10	V
DC Drain Current	I_D	100	mA
Drain Power Dissipation	P_D	100	mW
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$



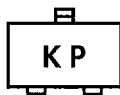
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Weight : 0.006g

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = 10V, V_{DS} = 0$	—	—	1	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 100\mu A, V_{GS} = 0$	20	—	—	V
Drain Cut-off Current		I_{DSS}	$V_{DS} = 20V, V_{GS} = 0$	—	—	1	μA
Gate Threshold Voltage		V_{th}	$V_{DS} = 3V, I_D = 0.1mA$	0.5	—	1.5	V
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 3V, I_D = 10mA$	25	50	—	mS
Drain-Source ON Resistance		$R_{DS(ON)}$	$I_D = 10mA, V_{GS} = 2.5V$	—	8	12	Ω
Input Capacitance		C_{iss}	$V_{DS} = 3V, V_{GS} = 0, f = 1MHz$	—	8.5	—	pF
Reverse Transfer Capacitance		C_{rss}	$V_{DS} = 3V, V_{GS} = 0, f = 1MHz$	—	3.3	—	pF
Output Capacitance		C_{oss}	$V_{DS} = 3V, V_{GS} = 0, f = 1MHz$	—	9.3	—	pF
Switching Time	Turn-on Time	t_{on}	$V_{DD} = 3V, I_D = 10mA$ $V_{GS} = 0 \sim 2.5V$	—	0.16	—	μs
	Turn-off Time	t_{off}	$V_{DD} = 3V, I_D = 10mA$ $V_{GS} = 0 \sim 2.5V$	—	0.15	—	μs



MARKING



THIS TRANSISTOR ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

SWITCHING TIME TEST CIRCUIT

